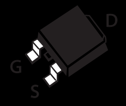
A1 **N-Channel Enhancement Mode MOSFET**

ASM3055x2

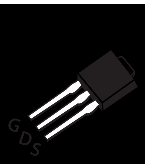
PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ)
25V	12A	60 @ V_{GS} = 10V
		85 @ V_{GS} = 4.5V

FEATURES

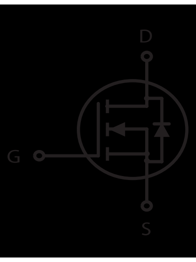
- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- TO252 and TO251 Package



STU SERIES
TO-252AA(D-PAK)



STD SERIES
TO-251(I-PAK)



ABSOLUTE MAXIMUM RATINGS (Tc=25. unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage Rating	V_{spike}[c]	30	V
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	±16	V
Drain Current-Continuous @Tc=25℃	I_D	12	A
-Pulsed[a]	I_{DM}	40	A
Drain-Source Diode Forward Current	I_S	5	A
Maximum Power Dissipation @Tc=25℃	P_D	50	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C
THERMAL CHARACTERISTICS			
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	°C/W